Dual supply translating buffer Rev. 1 — 22 December 2015

Product data sheet

General description

The 74AXP1T34 is a dual supply translating buffer. It features one input (A), an output (Y) and dual supply pins (V_{CCI} and V_{CCO}). The inputs are referenced to V_{CCI} and the output is referenced to V_{CCO}. All inputs can be connected directly to V_{CCI} or GND. V_{CCI} can be supplied at any voltage between 0.7 V and 2.75 V and V_{CCO} can be supplied at any voltage between 1.2 V and 5.5 V. This feature allows voltage level translation.

Schmitt-trigger action at all inputs makes the circuit tolerant of slower input rise and fall times.

This device ensures very low static and dynamic power consumption across the entire supply range and is fully specified for partial power down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the potentially damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range:
 - V_{CCI}: 0.7 V to 2.75 V
 - V_{CCO}: 1.2 V to 5.5 V
- Low input capacitance; C_I = 0.6 pF (typical)
- Low output capacitance; C_O = 1.8 pF (typical)
- Low dynamic power consumption; C_{PD} = 0.4 pF at V_{CCI} = 1.2 V (typical)
- Low dynamic power consumption; C_{PD} = 7.1 pF at V_{CCO} = 3.3 V (typical)
- Low static power consumption; I_{CCI} = 0.5 μA (85 °C maximum)
- Low static power consumption; I_{CCO} = 1.8 μA (85 °C maximum)
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-12A.01 (1.1 V to 1.3 V; A input)
 - ◆ JESD8-11A.01 (1.4 V to 1.6 V)
 - ◆ JESD8-7A (1.65 V to 1.95 V)
 - ◆ JESD8-5A.01 (2.3 V to 2.7 V)
 - ◆ JESD8-C (2.7 V to 3.6 V; Y output)
 - JESD12-6 (4.5 V to 5.5 V; Y output)
- ESD protection:
 - HBM ANSI/ESDA/JEDEC JS-001 Class 2 exceeds 2 kV
 - CDM JESD22-C101E exceeds 1000 V
- Latch-up performance exceeds 100 mA per JESD78D Class II
- Inputs accept voltages up to 2.75 V



- Low noise overshoot and undershoot < 10% of V_{CCO}
- I_{OFF} circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C

3. Ordering information

Table 1. Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
74AXP1T34GW	–40 °C to +85 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1						
74AXP1T34GM	–40 °C to +85 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886						
74AXP1T34GN	–40 °C to +85 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115						
74AXP1T34GS	–40 °C to +85 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202						
74AXP1T34GX	-40 °C to +85 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226						

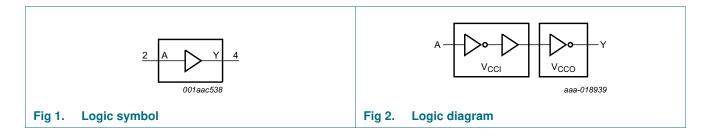
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AXP1T34GW	rQ
74AXP1T34GM	rQ
74AXP1T34GN	rQ
74AXP1T34GS	rQ
74AXP1T34GX	rQ

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

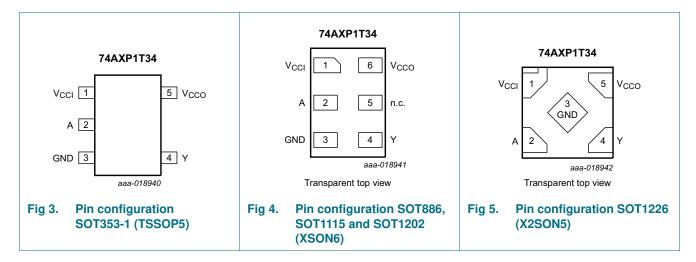
5. Functional diagram



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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Pin			
	TSSOP5 and X2SON5	XSON6			
V _{CCI}	1	1	input supply voltage		
A	2	2	data input A		
GND	3	3	ground (0 V)		
Υ	4	4	data output Y		
n.c.	-	5	not connected		
V _{CCO}	5	6	output supply voltage		

7. Functional description

Table 4. Function table[1]

Supply voltage		Input	Output		
V _{CCI} V _{CCO}		A	Υ		
0.7 V to 2.75 V	1.2 V to 5.5 V	L	L		
0.7 V to 2.75 V	1.2 V to 5.5 V	Н	Н		
GND	1.2 V to 5.5 V	X	Z		
0.7 V to 2.75 V	GND	X	Z		
GND	GND	X	Z		

[1] H = HIGH voltage level; L = LOW voltage level.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CCI}	input supply voltage		-0.5	3.3	V
V _{CCO}	output supply voltage		-0.5	6.0	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage	[1]	-0.5	3.3	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode [1][2]	-0.5	V _{CCO} + 0.5	V
		Power-down or 3-state mode	-0.5	6.0	V
Io	output current	V _O = 0 V to V _{CCO}	-	±25	mA
I _{CCI}	input supply current		-	50	mA
I _{CCO}	output supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +85 ^{\circ}\text{C}$	-	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CCI}	input supply voltage		0.7	2.75	V
V_{CCO}	output supply voltage		1.2	5.5	V
VI	input voltage		0	2.75	V
V _O	output voltage	Active mode	0	V _{CCO}	V
		Power-down or 3-state mode	0	5.5	V
T _{amb}	ambient temperature		-40	+85	°C
Δt/ΔV	input transition rise and fall rate	V _{CCI} = 0.7 V to 2.75 V	0	200	ns/V

^[2] $V_{CCO} + 0.5 \text{ V}$ should not exceed 6.0 V.

^[3] For SOT353-1 package: above 75 °C the value of P_{tot} derates linearly with 3.3 mW/K. For SOT886 package: above 75 °C the value of P_{tot} derates linearly with 3.3 mW/K. For SOT1115 package: above 70 °C the value of P_{tot} derates linearly with 3.2 mW/K. For SOT1202 package: above 75 °C the value of P_{tot} derates linearly with 3.3 mW/K. For SOT1226 package: above 70 °C the value of P_{tot} derates linearly with 3.1 mW/K.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions, unless otherwise specified; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			$T_{amb} = -40$	°C to +85 °	C	Unit
				Min	Typ 25 °C	Max 25 °C	Max 85 °C	
V _{IH}	HIGH-level input	V _{CCI} = 0.75 V to 0.85 V		0.75V _{CCI}	-	-	-	V
	voltage	V _{CCI} = 1.1 V to 1.95 V		0.65V _{CCI}	-	-	-	V
		V _{CCI} = 2.3 V to 2.7 V		1.6	-	-	-	V
V _{IL}	LOW-level input	V _{CCI} = 0.75 V to 0.85 V		-	-	0.25V _{CCI}	0.25V _{CCI}	V
	voltage	V _{CCI} = 1.1 V to 1.95 V		-	-	0.35V _{CCI}	0.35V _{CCI}	V
		V _{CCI} = 2.3 V to 2.7 V		-	-	0.7	0.7	V
V _{OH}	HIGH-level output	$I_{O} = -2 \text{ mA}; V_{CCO} = 1.2 \text{ V}$	[1]	-	1.05	-	-	V
	voltage	$I_{O} = -3 \text{ mA}; V_{CCO} = 1.4 \text{ V}$		1.05	-	-	-	V
		$I_O = -4.5 \text{ mA}; V_{CCO} = 1.65 \text{ V}$		1.2	-	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CCO} = 2.3 \text{ V}$		1.7	-	-	-	V
		$I_{O} = -10 \text{ mA}; V_{CCO} = 3.0 \text{ V}$		2.2	-	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CCO} = 4.5 \text{ V}$		3.7	-	-	-	V
V_{OL}	LOW-level output	I _O = 2 mA; V _{CCO} = 1.2 V	[1]	-	0.18	-	-	V
	voltage	I _O = 3 mA; V _{CCO} = 1.4 V		-	-	0.35	0.35	٧
		I _O = 4.5 mA; V _{CCO} = 1.65 V		-	-	0.45	0.45	٧
		I _O = 8 mA; V _{CCO} = 2.3 V		-	-	0.7	0.7	٧
		I _O = 10 mA; V _{CCO} = 3.0 V		-	-	0.8	0.8	٧
		I _O = 12 mA; V _{CCO} = 4.5 V		-	-	0.8	0.8	V
l _l	input leakage current	V _I = 0 V to 2.75 V; V _{CCI} = 0 V to 2.75 V	[1]	-	±0.001	±0.1	±0.5	μА
l _{OZ}	OFF-state output current	V _O = 0 V to 5.5 V; V _{CCO} = 1.2 V to 5.5 V		-	±0.001	±0.1	±0.5	μА
l _{OFF}	power-off leakage current	inputs; V _I = 0 V to 2.75 V; V _{CCI} = 0 V; V _{CCO} = 0 V to 5.5 V	[1]	-	±0.01	±0.1	±0.5	μΑ
		output; $V_O = 0 \text{ V to } 5.5 \text{ V};$ $V_{CCO} = 0 \text{ V}; V_{CCI} = 0 \text{ V to } 2.75 \text{ V};$ $V_I = 0 \text{ V to } 2.75 \text{ V}$	[1]	-	±0.01	±0.1	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	inputs; $V_I = 0 \text{ V or } 2.75 \text{ V};$ $V_{CCI} = 0 \text{ V to } 0.1 \text{ V};$ $V_{CCO} = 0 \text{ V to } 5.5 \text{ V}$	[1]	-	±0.02	±0.1	±0.5	μА
		output; $V_O = 0 \text{ V or } 5.5 \text{ V};$ $V_{CCO} = 0 \text{ V to } 0.1 \text{ V};$ $V_{CCI} = 0 \text{ V to } 2.75 \text{ V};$ $V_I = 0 \text{ V or } 2.75 \text{ V}$	[1]	-	±0.02	±0.1	±0.5	μА

^[1] Typical values are measured at $V_{\text{CCI}} = V_{\text{CCO}} = 1.2 \text{ V}$ unless otherwise specified.

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Table 8. Static characteristics supply current

At recommended operating conditions, unless otherwise specified; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		$T_{amb} = -40^{\circ}$	°C to +85 °C		Unit
			Typ 25 °C	Max 25 °C	Typ 85 °C	Max 85 °C	
I _{CCI}	input supply	$V_I = 0 V \text{ or } V_{CCI};$					
	current	V _{CCI} = 0.7 V to 1.3 V	1	100	10	300	nA
		V _{CCI} = 1.3 V to 2.75 V	1	100	20	500	nA
		$V_{CCI} = 2.75 \text{ V}; V_{CCO} = 0 \text{ V}$	1	100	20	500	nA
		V _{CCI} = 0 V; V _{CCO} = 5.5 V	1	100	1	100	nA
I _{CCO}	output supply current	$V_I = 0 \text{ V or } V_{CCI}; I_O = 0 \text{ A};$ see <u>Table 9</u>					
		V _{CCO} = 1.2 V to 3.6 V	0.001	1.0	0.01	1.2	μΑ
		V _{CCO} = 3.6 V to 5.5 V	8.0	1.5	1.0	1.8	μΑ
		V _{CCI} = 2.75 V; V _{CCO} = 0 V	0.001	0.1	0.003	0.2	μΑ
		V _{CCI} = 0 V; V _{CCO} = 3.6 V	0.2	0.6	0.3	0.8	μΑ
		V _{CCI} = 0 V; V _{CCO} = 5.5 V	0.4	0.8	0.5	1.0	μΑ
Δl _{CCI}	additional input supply current	$V_I = V_{CCI} - 0.5 \text{ V}; V_{CCI} = 2.5 \text{ V}$	2	100	14	150	μΑ

^[1] Typical values are measured at $V_{CCI} = V_{CCO} = 1.2 \text{ V}$.

Table 9. Typical output supply current (I_{CCO})

V _{CCI}	V _{cco}	V _{cco}								
	0 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V			
0 V	0	1	5	20	100	200	400	nA		
0.8 V	1	10	150	200	300	500	800	nA		
1.2 V	1	1	5	200	300	500	800	nA		
1.5 V	1	1	5	100	300	500	800	nA		
1.8 V	1	1	5	100	300	500	800	nA		
2.5 V	1	1	5	100	100	500	800	nA		

^[2] Typical values are measured at $V_{CCI} = V_{CCO} = 2.5 \text{ V}$.

^[3] Typical values are measured at V_{CCI} = 1.2 V and V_{CCO} = 5.0 V.

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11. Dynamic characteristics

Table 10. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13; for wave form see Figure 6.

Symbol	Parameter	Conditions				V _{cco}				Unit
			1.2 V	1	.5 V ± 0.1	V	1.8	8 V ± 0.15	٧	
			Typ[1]	Min	Typ[1]	Max	Min	Typ[1]	Max	
T _{amb} = 2	5 °C									
t _{pd}	propagation	A to Y								
	delay	V _{CCI} = 0.75 V to 0.85 V	22	3	16	61	3	15	57	ns
		V _{CCI} = 1.1 V to 1.3 V	16.2	3.1	10.3	19.8	2.8	8.2	15.8	ns
		V _{CCI} = 1.4 V to 1.6 V	15.4	2.8	9.5	18.2	2.5	7.4	13.2	ns
		V _{CCI} = 1.65 V to 1.95 V	15.0	2.7	9.1	17.4	2.4	7.0	11.9	ns
		V _{CCI} = 2.3 V to 2.7 V	14.7	2.5	8.7	16.9	2.2	6.6	11.1	ns
T _{amb} = -	40 °C to +85 °	°C								
t _{pd}	propagation	A to Y								
	delay	V _{CCI} = 0.75 V to 0.85 V	22	3	16	136	3	15	133	ns
		V _{CCI} = 1.1 V to 1.3 V	16.2	3.1	10.3	19.8	2.8	8.2	15.8	ns
		V _{CCI} = 1.4 V to 1.6 V	15.4	2.8	9.5	18.2	2.5	7.4	13.2	ns
		V _{CCI} = 1.65 V to 1.95 V	15.0	2.7	9.1	17.4	2.4	7.0	11.9	ns
		V _{CCI} = 2.3 V to 2.7 V	14.7	2.5	8.7	16.9	2.2	6.6	11.1	ns
t _t	transition time	$V_{CCI} = 0.75 \text{ V to } 2.7 \text{ V}$	-	1.0	-	-	1.0	-	-	ns

^[1] Typical values are measured at nominal supply voltages and T_{amb} = +25 °C.

^[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

^[3] t_t is the same as t_{THL} and t_{TLH} .

Dual supply translating buffer

Table 11. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13; for wave form see Figure 6.

Symbol	Parameter	Conditions		V _{cco}								Unit
			2	.5 V ± 0.2	2 V	3.3	3 V ± 0.3	V	5.0	V ± 0.5	V	
			Mir	Typ[1]	Max	Min	Typ[1]	Max	Min	Typ[1]	Max	-
T _{amb} = 2	5 °C			1								
t _{pd}	propagation	A to Y	[2]									
	delay	$V_{CCI} = 0.75 \text{ V to } 0.85 \text{ V}$	2	13	57	2	13	65	2	14	77	ns
		V _{CCI} = 1.1 V to 1.3 V	2.4	6.5	10.8	2.2	5.9	9.5	2.1	5.6	9.0	ns
		V _{CCI} = 1.4 V to 1.6 V	2.1	5.7	9.1	2.0	5.1	8.2	1.9	4.8	7.7	ns
		V _{CCI} = 1.65 V to 1.95 V	2.0	5.3	8.7	1.8	4.7	7.7	1.8	4.4	7.3	ns
		V _{CCI} = 2.3 V to 2.7 V	1.9	4.9	8.1	1.7	4.3	7.1	1.6	4.0	6.6	ns
T _{amb} = -	40 °C to +85	°C										
t _{pd}	propagation	A to Y	[2]									
	delay	V _{CCI} = 0.75 V to 0.85 V	2	13	152	2	13	179	2	14	210	ns
		V _{CCI} = 1.1 V to 1.3 V	2.4	6.5	10.8	2.2	5.9	9.5	2.1	5.6	9.0	ns
		V _{CCI} = 1.4 V to 1.6 V	2.1	5.7	9.1	2.0	5.1	8.2	1.9	4.8	7.7	ns
		V _{CCI} = 1.65 V to 1.95 V	2.0	5.3	8.7	1.8	4.7	7.7	1.8	4.4	7.3	ns
		V _{CCI} = 2.3 V to 2.7 V	1.9	4.9	8.1	1.7	4.3	7.1	1.6	4.0	6.6	ns
t _t	transition time	$V_{CCI} = 0.75 \text{ V to } 2.7 \text{ V}$	1.0	-	-	1.0	-	-	1.0	-	-	ns

^[1] Typical values are measured at nominal supply voltages and t_{amb} = +25 °C.

^[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

^[3] t_t is the same as t_{THL} and t_{TLH} .

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Table 12. Typical dynamic characteristics at T_{amb} = 25 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13; for wave form see Figure 6.

		10 //								
Symbol	Parameter	Conditions				Vo	со			Unit
				1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V	
C _{PD}	power	f_i = 1 MHz; R_L = ∞ Ω ; V_I = 0 V to V_{CCI}	[1]							
	dissipation capacitance	input supply	[2]							
	capacitarice	V _{CCI} = 0.8 V		0.4	0.4	0.4	0.4	0.4	0.4	pF
		V _{CCI} = 1.2 V		0.4	0.4	0.4	0.4	0.4	0.4	pF
		V _{CCI} = 1.5 V		0.5	0.5	0.5	0.5	0.5	0.5	pF
		V _{CCI} = 1.8 V		0.5	0.5	0.5	0.5	0.5	0.5	pF
		V _{CCI} = 2.5 V		0.7	0.7	0.7	0.7	0.7	0.7	pF
		output supply	[3]							
		V _{CCI} = 0.8 V		6.7	6.8	6.8	6.9	7.5	9.5	pF
		V _{CCI} = 1.2 V		6.8	6.9	7.0	7.0	7.1	7.6	pF
		V _{CCI} = 1.5 V		6.9	6.9	6.9	7.0	7.1	7.6	pF
		V _{CCI} = 1.8 V		6.9	6.9	6.9	7.0	7.2	7.6	pF
		V _{CCI} = 2.5 V		6.9	7.0	7.0	7.0	7.2	7.6	pF
Cı	input capacitance	$V_I = 0 \text{ V or } V_{CCI}; V_{CCI} = 0 \text{ V to } 2.7 \text{ V}$		0.6	0.6	0.6	0.6	0.6	0.6	pF
Co	output capacitance	$V_O = 0 \text{ V}; V_{CCO} = 0 \text{ V}$		1.8	1.8	1.8	1.8	1.8	1.8	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

[2] Power dissipated from input supply (V_{CCI})

 $P_D = C_{PD} \times V_{CCI}{}^2 \times f_i \times N$ where:

C_{PD} = power dissipation capacitance of the input supply.

 V_{CCI} = input supply voltage in V;

 f_i = input frequency in MHz;

N = number of inputs switching;

[3] Power dissipated from output supply (V_{CCO})

 $P_D = (C_L + C_{PD}) \times V_{CCO}^2 \times f_o$ where:

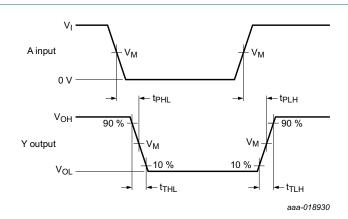
C_L = load capacitance in pF;

 C_{PD} = power dissipation capacitance of the output supply.

 V_{CCO} = output supply voltage in V;

 $f_o = output frequency in MHz;$

11.1 Waveforms and graphs



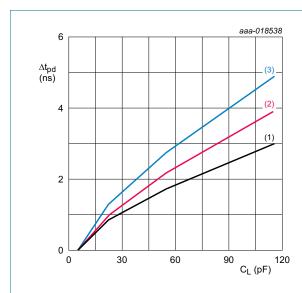
Measurement points are given in Table 13.

 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. Input A to output Y propagation delay times and output transition times

Table 13. Measurement points

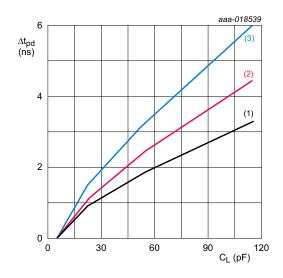
Supply voltage		Output	Input			
V _{CCI}	V _{CCO}	V _M	V _M	VI		
0.75 V to 2.7 V	1.2 V to 5.5 V	0.5V _{CCO}	0.5V _{CCI}	V _{CCI}		



 $T_{amb} = -40 \, ^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$ unless otherwise specified.

- (1) Minimum: $V_{CCO} = 5.5 \text{ V}$
- (2) Typical: $T_{amb} = 25 \,^{\circ}C$; $V_{CCO} = 5 \,^{\circ}V$
- (3) Maximum: V_{CCO} = 4.5 V

Fig 7. Additional propagation delay versus load capacitance

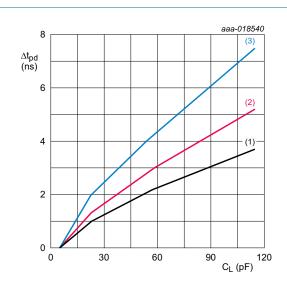


 T_{amb} = -40 °C to +85 °C unless otherwise specified.

- (1) Minimum: $V_{CCO} = 3.6 \text{ V}$
- (2) Typical: $T_{amb} = 25 \, ^{\circ}C$; $V_{CCO} = 3.3 \, V$
- (3) Maximum: $V_{CCO} = 3 V$

Fig 8. Additional propagation delay versus load capacitance

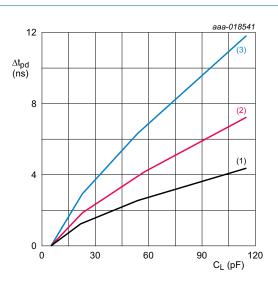
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 T_{amb} = -40 °C to +85 °C unless otherwise specified.

- (1) Minimum: $V_{CCO} = 2.7 \text{ V}$
- (2) Typical: $T_{amb} = 25 \,^{\circ}C$; $V_{CCO} = 2.5 \,^{\circ}V$
- (3) Maximum: V_{CCO} = 2.3 V

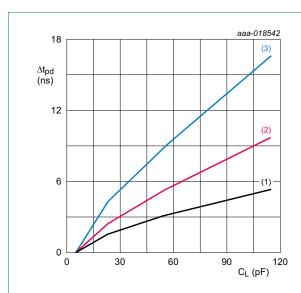
Fig 9. Additional propagation delay versus load capacitance



 T_{amb} = -40 °C to +85 °C unless otherwise specified.

- (1) Minimum: $V_{CCO} = 1.95 \text{ V}$
- (2) Typical: $T_{amb} = 25 \, ^{\circ}C$; $V_{CCO} = 1.8 \, V$
- (3) Maximum: V_{CCO} = 1.65 V

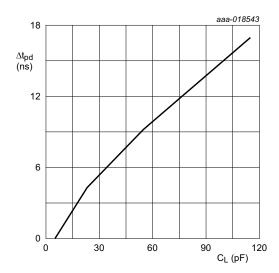
Fig 10. Additional propagation delay versus load capacitance



 $T_{amb} = -40 \, ^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$ unless otherwise specified.

- (1) Minimum: $V_{CCO} = 1.6 \text{ V}$
- (2) Typical: $T_{amb} = 25 \, ^{\circ}\text{C}$; $V_{CCO} = 1.5 \, \text{V}$
- (3) Maximum: V_{CCO} = 1.4 V

Fig 11. Additional propagation delay versus load capacitance



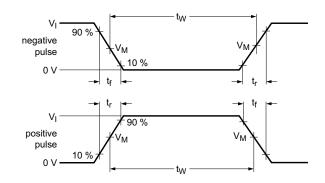
 T_{amb} = 25 °C; V_{CCO} = 1.2 V.

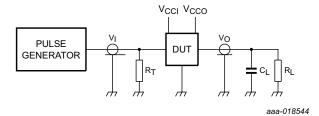
Fig 12. Additional propagation delay versus load capacitance

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Test data is given in Table 14.

Definitions test circuit:

 R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = load capacitance including jig and probe capacitance.

 R_L = Load resistance.

Fig 13. Test circuit for measuring switching times

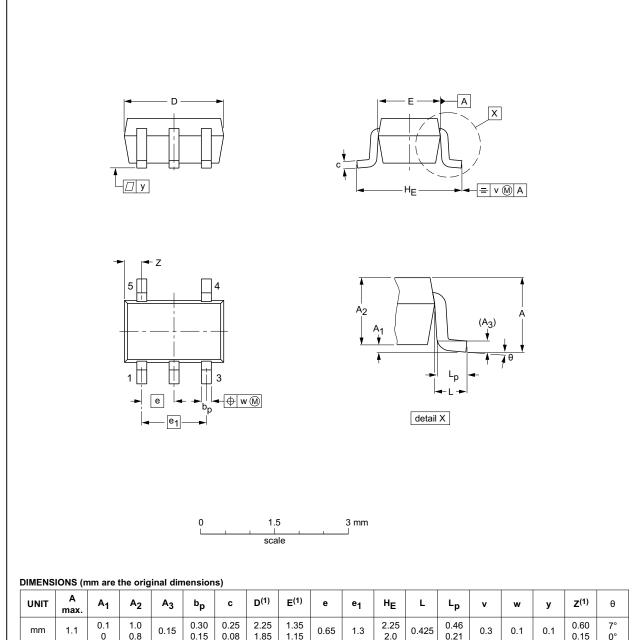
Table 14. Test data

Supply voltage		Load		Input		
V _{CCI}	V _{CCO}	CL	R _L	t _r , t _f	VI	
0.75 V to 2.7 V	1.2 V to 5.5 V	5 pF	5 kΩ	≤3.0 ns	V _{CCI}	

12. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A ₁	A ₂	Α3	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	HE	L	Lp	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT353-1		MO-203	SC-88A			00-09-01 03-02-19

Fig 14. Package outline SOT353-1 (TSSOP5)

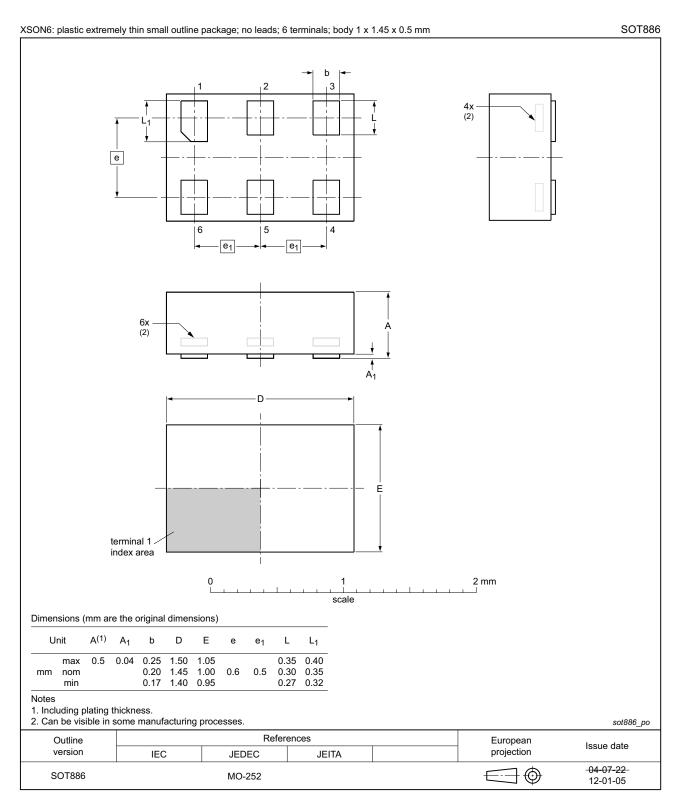


Fig 15. Package outline SOT886 (XSON6)

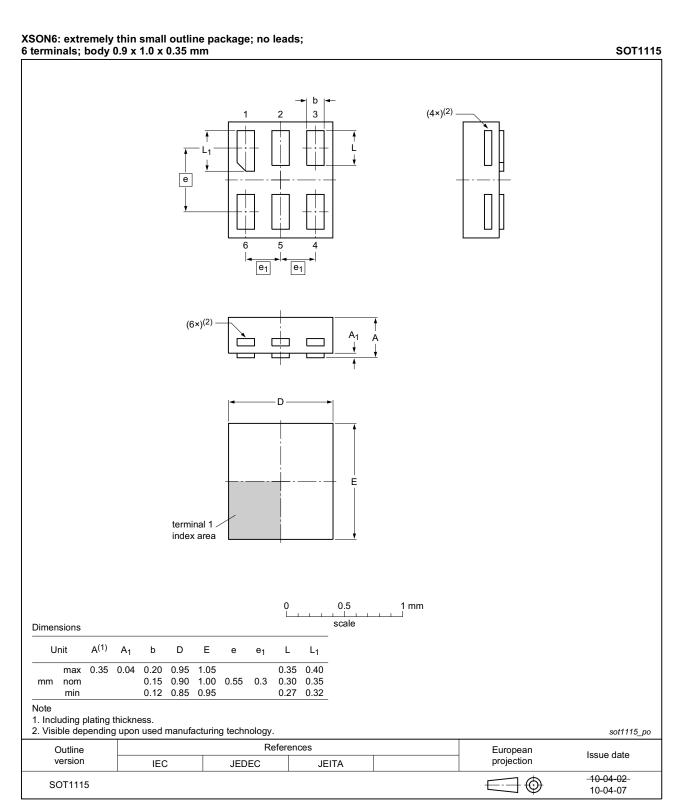


Fig 16. Package outline SOT1115 (XSON6)

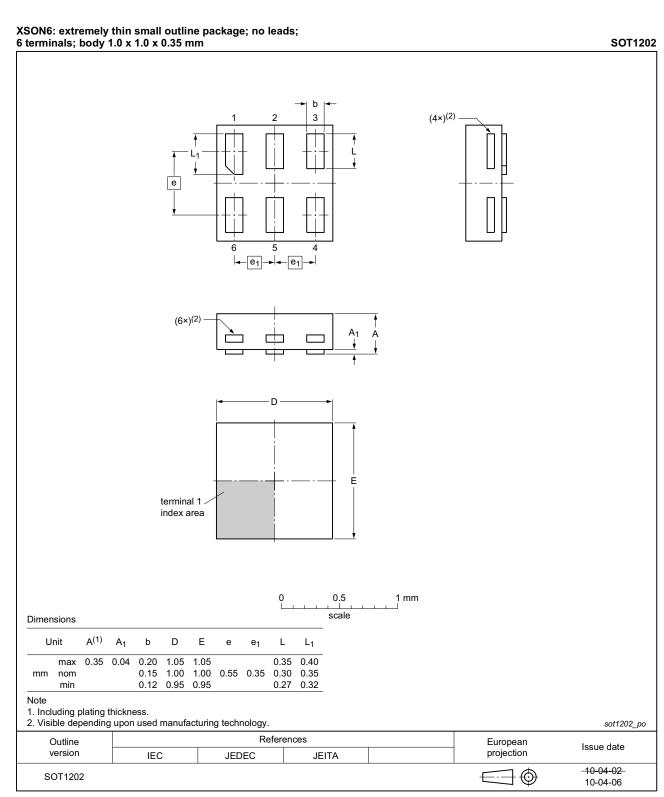


Fig 17. Package outline SOT1202 (XSON6)

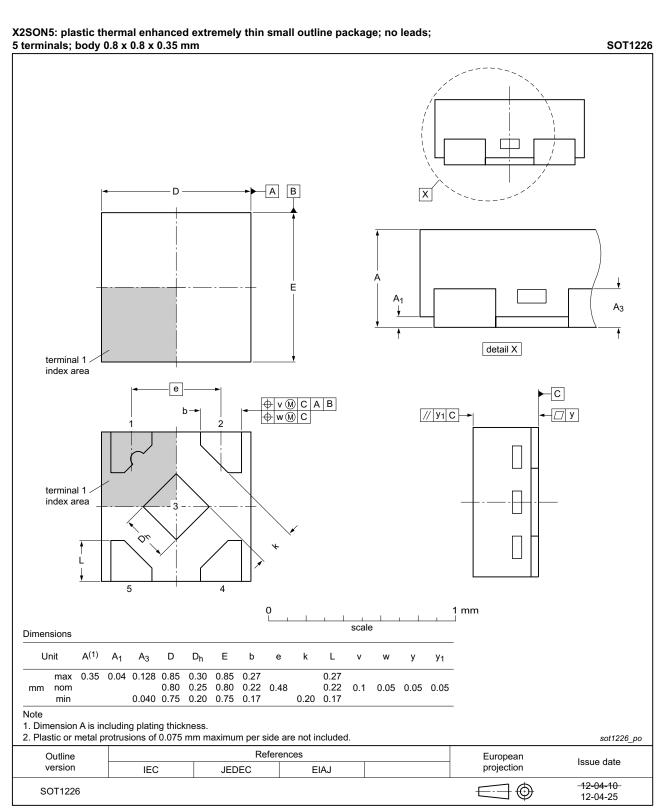


Fig 18. Package outline SOT1226 (X2SON5)

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13. Abbreviations

Table 15. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model

14. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AXP1T34 v.1	20151222	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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